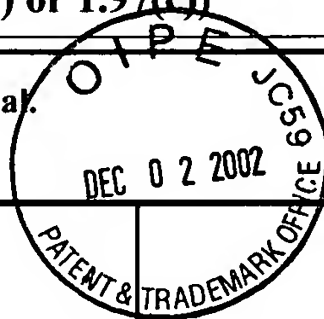


Supplemental

GP/2811

<b>TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT</b> (Under 37 CFR 1.97(b) or 1.97(c))		Docket No. GS 174	
In Re Application Of: <b>Richard A. Blanchard et al.</b>			
Serial No. <b>10/039,284</b>	Filing Date <b>12/31/01</b>	Examiner <b>Unassigned</b>	Group Art Unit <b>2811</b>
Title: <b>HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY TRENCH ETCHING USING AN ETCHANT GAS THAT IS ALSO A DOPING SOURCE</b>			
Address to: <b>Assistant Commissioner for Patents Washington, D.C. 20231</b>			
<b>37 CFR 1.97(b)</b>			
1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.			
<b>37 CFR 1.97(c)</b>			
2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:			
<input type="checkbox"/> the statement specified in 37 CFR 1.97(e);			
<b>OR</b>			
<input type="checkbox"/> the fee set forth in 37 CFR 1.17(p).			



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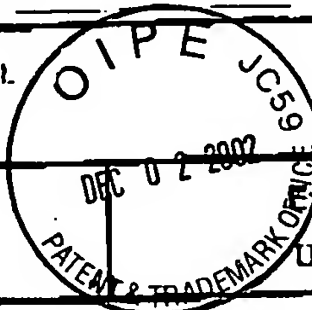
**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
GS 174

In Re Application: Richard A. Blanchard et al.

Serial No.  
10/039,284

Filing Date  
12/31/01



Examiner  
Unassigned

Group Art Unit  
2811

**HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION  
THAT INCLUDES DOPED COLUMNS FORMED BY TRENCH ETCHING USING AN  
ETCHANT GAS THAT IS ALSO A DOPING SOURCE**

**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☐ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. \_\_\_\_\_ as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of \_\_\_\_\_
- ☐ Credit any overpayment.
- ☐ Charge any additional fee required.

**Certificate of Transmission by Facsimile\***

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**Certificate of Mailing by First Class Mail**

I certify that this document and fee is being deposited with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

11/27/02

\_\_\_\_\_  
Signature of Person Mailing Correspondence

Marjorie Seariani

\_\_\_\_\_  
Typed or Printed Name of Person Mailing Certificate

\*This certificate may only be used if paying by deposit account.

Karin L. Williams  
Signature


Dated: 11/27/02

Karin L. Williams Reg. No. 36,721  
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251 North Avenue West, 2nd Floor  
Westfield, NJ 07090


Tel.: 908-518-7700  
Fax: 908-518-7795

CC:

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Supplemental <b>INFORMATION DISCLOSURE CITATION</b> ^ (Use several sheets if necessary)				ATTY DOCKET NO. <b>GS 174</b>		SERIAL NO. <b>10/039,284</b>	
				Richard A. Blanchard et al.		GROUP <b>2811</b>	
				FILING <b>12/31/01</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	1.	10/039,241		Blanchard			12/31/2001
	2.	10/038,845		Blanchard			12/31/2001
	3.	09/970,758		Blanchard et al.			10/4/2001
	4.	2001/0053568A1	12/20/2001	Deboy et al.	438	138	
	5.	2001/0036704A1	11/1/2001	Huetting et al.	438	270	
	6.	2001/0026977A1	10/4/2001	Hattori et al.	438	268	
	7.	5,216,275	6/1/93	Chen	257	493	
	8.	5,108,783	4/28/92	Tanigawa et al.	437	63	
	9.	4,893,160	1/9/90	Blanchard	357	23.4	
	10.	4,711,017	12/8/87	Lammert	437	20	
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
		1.	Xing Bi Chen et al., "A Novel High-Voltage Sustaining Structure with Buried Oppositely Doped Regions," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 6, June 2000, pp. 1280-1285.				
		2.	N. Cezac et al., "A New Generation of Power Unipolar Devices: the Concept of the Floating Islands MOS Transistor (FLIMOST)," Proceedings of the 12th International Symposium on Power Semiconductor Devices & ICs, Toulouse, France, May 22-25, 2000, pp. 69-72.				
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

<i>Supplemental</i> <b>INFORMATION DISCLOSURE CITATION</b> <small>(Use several sheets if necessary)</small>				ATTY DOCKET NO. <b>GS 174</b>		SERIAL NO. <b>10/039,284</b>	
				<b>Richard A. Blanchard et al.</b>			
				FILING <b>12/31/01</b>		GROUP <b>2811</b>	



PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	11.	4,569,701	2/11/86	Oh	148	188	
	12.	4,419,150	12/6/83	Soclof	148	187	
	13.	4,140,558	2/20/79	Murphy et al.	148	175	
	14.	10/039,068		Blanchard			12/31/01

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
		3.	Ming-Kwang Lee et al., "On the Semi-Insulating Polycrystalline Silicon Resistor," <i>Solid State Electronics</i> Vol. 27, No. 11, 1984, pp. 995-1001.

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EXAMINER	DATE CONSIDERED

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